

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07217 DT-33-19

SILICON PNP TRIPLE DIFFUSED TYPE

2SA490

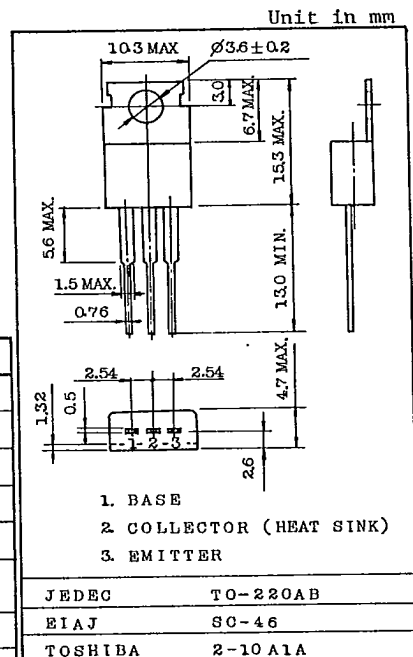
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Complementary to 2SC790.
- 10 Watts Output Applications.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-3	A
Emitter Current	I _E	3	A
Collector Power Dissipation (Tc=25°C)	P _C	25	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Mounting Kit No. AC75
Weight : 1.9g

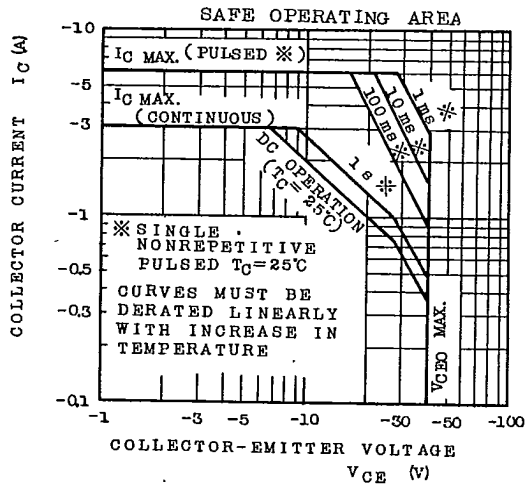
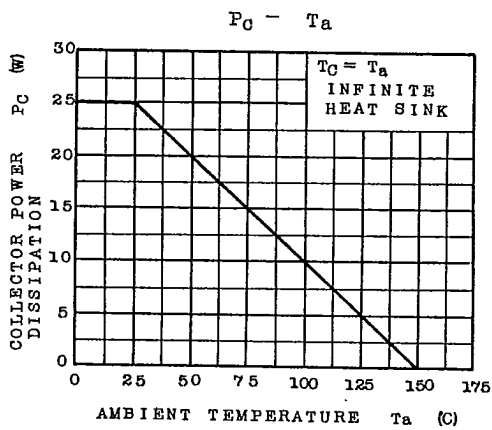
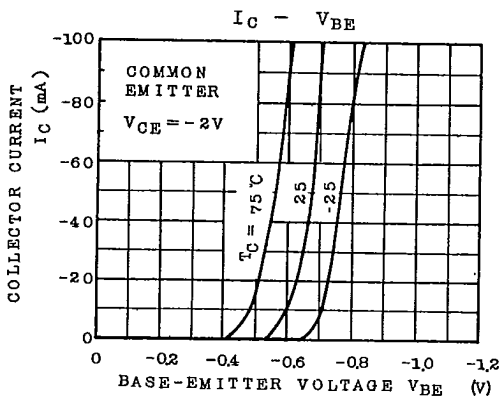
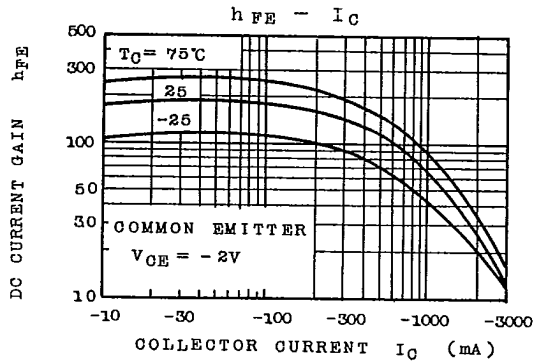
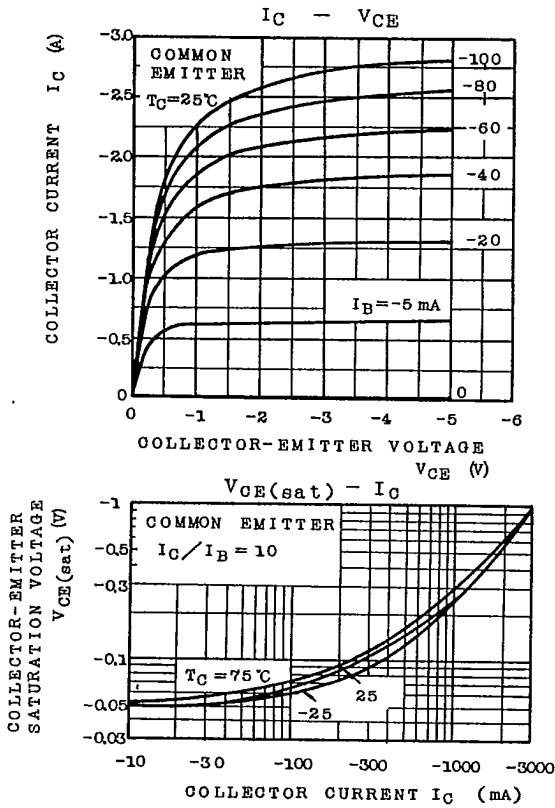
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =-30V, I _E =0	-	-	-10	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _C =0	-	-	-100	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-50mA, I _B =0	-40	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10mA, I _C =0	-5	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =-2V, I _C =-0.5A	40	-	240	
	h _{FE} (2)	V _{CE} =-2V, I _C =-2A	13	50	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-2A, I _B =-0.2A	-	-0.45	-1.2	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-2V, I _C =-2A	-	-0.85	-1.8	V
Transition Frequency	f _T	V _{CE} =-2V, I _C =-0.5A	3	10	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	150	-	pF

Note : h_{FE}(1) Classification R : 40~80 O : 70~140 Y : 120~240

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